

AMENDMENTS TO THE CLAIMS

Claim 1 (previously amended): A base plate for a power module, comprising:

a metal plate;

a ceramic base plate joined to the metal plate; and

a release agent provided in a joint surface between the metal plate and the ceramic base plate, wherein

a remaining amount of the release agent is less than 5 as an amount of boron measured by fluorescence X-ray analysis, and

a crystal grain straining region in the joint surface is equal to or less than 40%.

Claim 2 (previously amended): A base plate for a power module, comprising:

a metal plate;

a ceramic base plate joined to the metal plate; and

a release agent provided in a joint surface between the metal plate and the ceramic base plate, wherein

a remaining amount of the release agent is less than 5 as an amount of boron measured by fluorescence X-ray analysis, and

an amount of crystal grain straining in the joint surface is equal to or less than 0.03%.

Claim 3 (previously amended): The base plate for a power module according to claim 1, wherein

the metal plate is made of aluminum, and
the ceramic base plate is a plate made of any one of aluminum nitride and
silicon nitride.

Claim 4 (previously amended): A power module comprising:
the base plate for a power module according to claim 1;
and
a semiconductor chip mounted on the metal plate of the base plate for a power module.

Claim 5 (currently amended): An ~~Al/AIN~~ Al/AlN joint material comprising;
an aluminum member;
an aluminum nitride member joined to the aluminum member; and
a brazing material provided between the aluminum member and the aluminum nitride
member, wherein

the brazing material infiltrates in a porous layer on a surface of the aluminum nitride
member, and

at least a portion of the brazing material forms a three-dimensional network structure within
substantially equal to or more than 0.5 layers and equal to or less than three layers of a crystal
structure of the aluminum nitride member.

Claim 6 (currently amended): The ~~Al/AIN~~ Al/AlN joint material according to claim 5,
wherein

a diameter of the three-dimensional network structure is greater inside the aluminum nitride
member than on a surface of the aluminum nitride member.

Claim 7 (currently amended): A base plate for a power module, comprising:
an insulated base plate; and
a heat-releasing object provided on a first side of the insulated base plate,
wherein

the insulated base plate is the Al/AlNAl/AlN joint material according to claim 5.

Claim 8 (original): A power module comprising:
the base plate for a power module according to claim 7; and
a chip which is mounted on a second side of the insulated base plate.

Claim 9 (original): A power module comprising:
the base plate for a power module according to claim 7; and
a heat sink which is any one of air-cooled and water-cooled mounted on a
second side of the insulated base plate.

Claim 10 (currently amended): A manufacturing method of an Al/AlNAl/AlN joint material,
comprising:

a first step of obtaining an AlNAlN sintering body having a porous layer on a surface
thereof by sintering a powder of AlNAlN; and

a second step of joining an Al member of the porous layer via a brazing material.

Claim 11 (currently amended): The manufacturing method of an Al/AINAl/AlN joint material according to claim 10, further comprising

a third step of removing a weak porous layer formed on a surface of the AlNAlN sintering body on which the Al member is joined, wherein

in the second step, the Al member is joined on the surface via the brazing material.

Claim 12 (currently amended): The manufacturing method of an Al/MN Al/AlN joint material according to claim 11 further comprising

a fourth step of heating and pressurizing the AlNAlN sintering body and the Al member under vacuum, with the brazing material being provided between the AlNAlN sintering body and the Al member.

Claim 13 (currently amended): The manufacturing method of an Al/MNAl/AlN joint material according to claim 12, wherein

in the fourth step, a joint surface is set in a vacuum, a liquid phase occurs in the brazing material by heating, and the liquid of the brazing material is infiltrated in a porous layer of the AlNAlN sintering body.

Claim 14 (currently amended): The manufacturing method of an Al/AINAl/AlN joint material according to claim 12, wherein

in the second step, the Al member is joined to the AlNAlN sintering body by allowing the brazing material to infiltrate the porous layer of the AlNAlN sintering body by cooling and setting the liquid of the brazing material provided between the AlNAlN sintering body and the Al member.

Claim 15 (previously presented): The base plate for a power module according to claim 2, wherein

the metal plate is made of aluminum, and

the ceramic base plate is a plate made of any one of aluminum nitride and silicon nitride.

Claim 16 (previously presented): A power module comprising:

the base plate for a power module according to claim 2; and

a semiconductor chip mounted on the metal plate of the base plate for a power module.